PSMN1R0-30YLD

N-channel 30 V, 1.0 mΩ, 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions		Min	Tun	Max	Unit
Symbol	Farameter	Conditions		IVIIII	Тур	Wax	Unit
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	-	300	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	238	W
Tj	junction temperature			-55	-	175	°C
Static charac	teristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 10		-	1	1.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10		-	0.79	1.02	mΩ
Dynamic cha	racteristics						,
Q _{GD}	gate-drain charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 12; Fig. 13		-	10.9	16.35	nC
Q _{G(tot)}	total gate charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; Fig. 12; Fig. 13		-	38.2	57.3	nC
Source-drain	diode						
S	softness factor	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{DS} = 15 \text{ V}; \underline{\text{Fig. 16}}$		-	0.95	-	

[1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, Thermal design and operating temperature.

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G C C
4	G	gate	ប្រុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering inf	formation				
Type number	Package				
	Name	Description	Version		
PSMN1R0-30YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

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Marking 7.

Table 4. Marking codes	
Type number	Marking code
PSMN1R0-30YLD	1D030L

Limiting values 8.

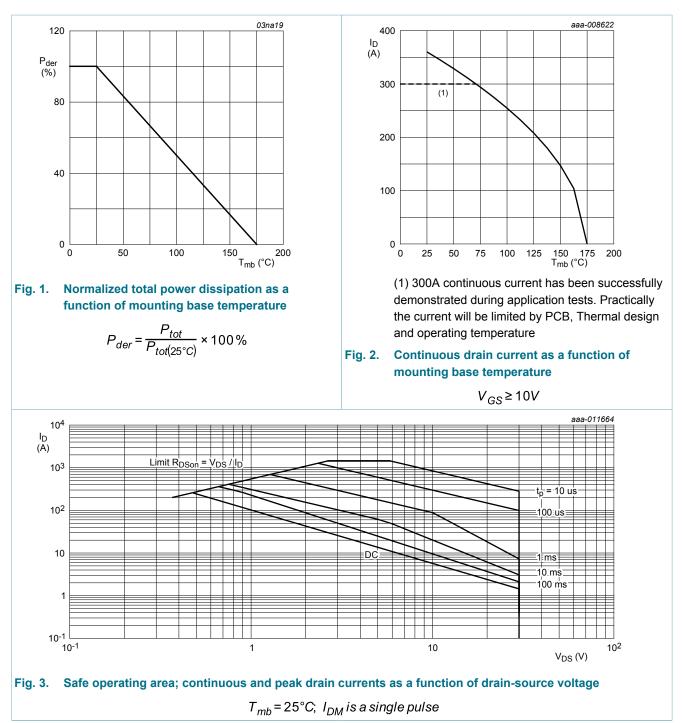
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 175 °C; R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	238	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	300	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	255	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	1441	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	НВМ		1500	-	V
Source-dra	in diode	1	1			
I _S	source current	T _{mb} = 25 °C		-	198	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1441	А
Avalanche	ruggedness	1				
I _{AS}	non-repetitive avalanche current	$\label{eq:V_sup} \begin{split} V_{sup} &\leq 30 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(\text{init})} = 25 ^{\circ}\text{C}; \\ $	[2]	-	190	A
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 25 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; unclamped; t_p = 3.3 ms	[2]	-	1588	mJ

[1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, Thermal design and operating temperature.

Protected by 100% test [2]

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9. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.56	0.63	K/W
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	Fig. 5	-	50	-	K/W
	from junction to ambient	<u>Fig. 6</u>	-	125	-	K/W

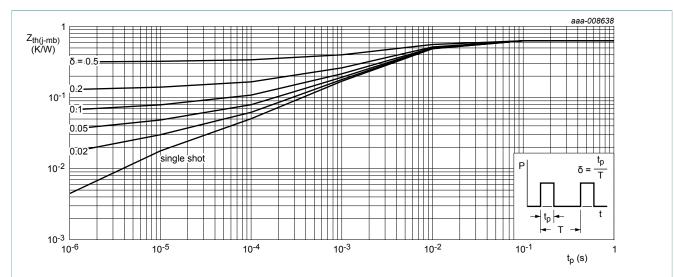
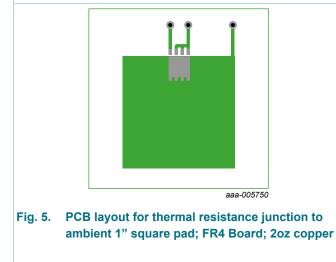


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration



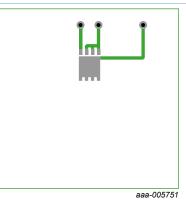


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	l.			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.75	2.2	V

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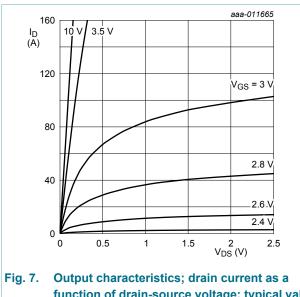
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔV _{GS(th)} /ΔT	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.9	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 24 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 24 V; V _{GS} = 0 V; T _j = 125 °C	-	2.8	-	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 10</u>	-	1	1.3	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; Fig. 11; Fig. 10	-	-	2.15	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	0.79	1.02	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 11; Fig. 10	-	-	1.7	mΩ
R _G	gate resistance	f = 1 MHz	-	1.22	2.44	Ω
Dynamic cha	aracteristics					J
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	80.9	121.35	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	38.2	57.3	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	72	-	nC
Q _{GS}	gate-source charge	I_D = 25 A; V_{DS} = 15 V; V_{GS} = 4.5 V;	-	12.5	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	7.8	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	4.7	-	nC
Q _{GD}	gate-drain charge		-	10.9	16.35	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.6	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	5732	8598	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	2424	3636	pF
C _{rss}	reverse transfer capacitance		-	340	510	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R _L = 1 Ω; V _{GS} = 4.5 V;	-	32.4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	44.4	-	ns
t _{d(off)}	turn-off delay time	1	-	43	-	ns
t _f	fall time		-	31.7	-	ns

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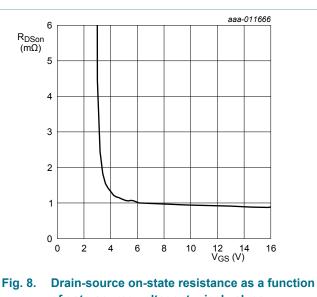
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C		-	55.9	-	nC
Source-dra	in diode			•			
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;		-	51.8	103.6	ns
Q _r	recovered charge	V _{DS} = 15 V; <u>Fig. 16</u>	[1]	-	67.1	134.2	nC
t _a	reverse recovery rise time			-	26.5	-	ns
t _b	reverse recovery fall time			-	25.3	-	ns
S	softness factor	-		-	0.95	-	



[1] includes capacitive recovery



function of drain-source voltage; typical values $T_i = 25^{\circ}C$

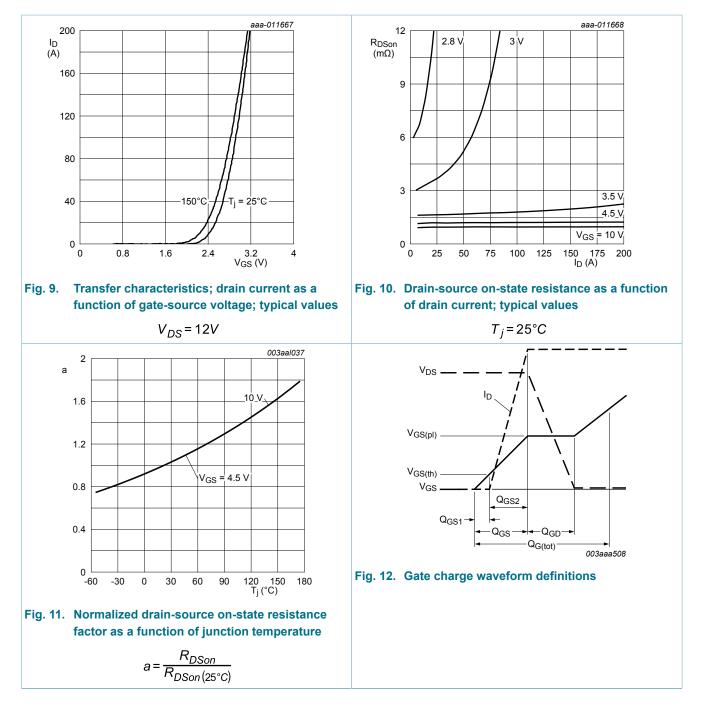


 $T_j = 25^{\circ}C; I_D = 25A$

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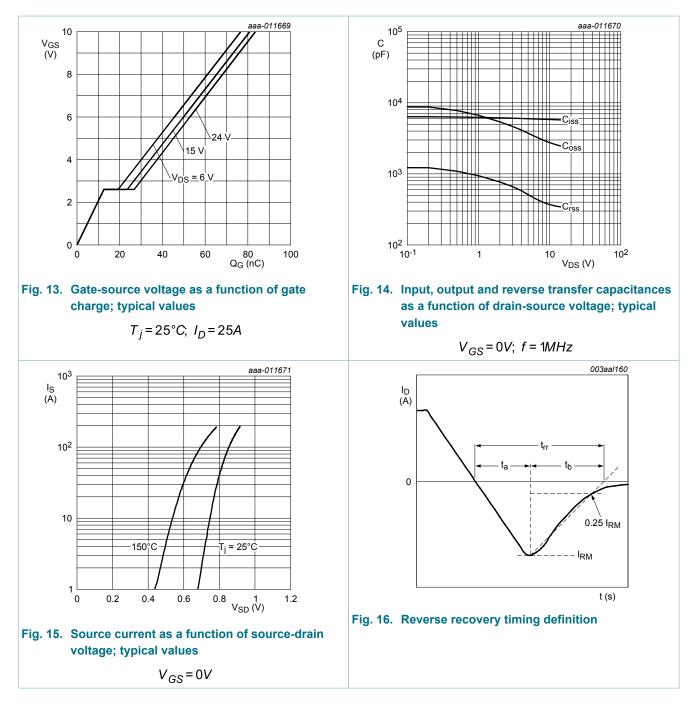
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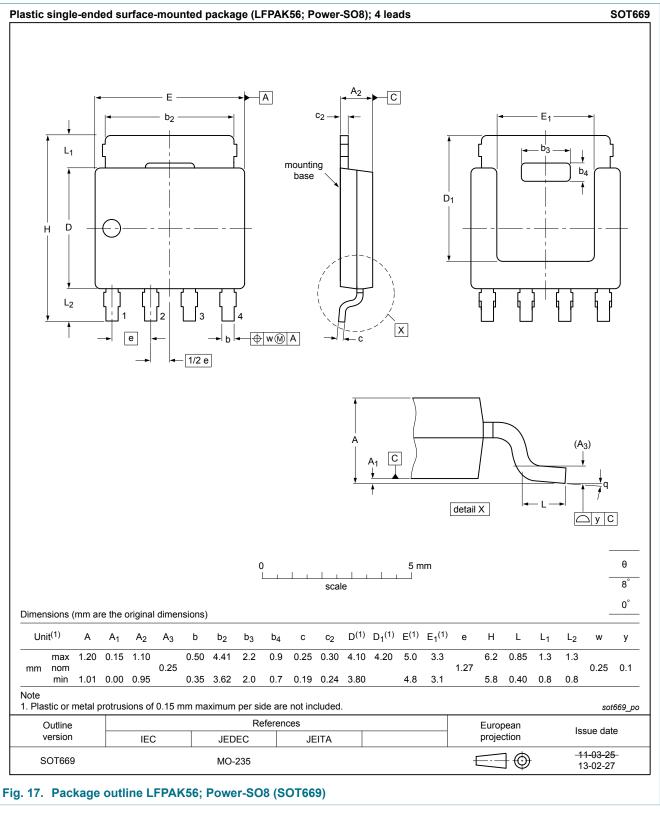
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11. Package outline



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Product data sheet

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12. Legal information

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